

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

1. - 16. (Canceled)

17. (Original) A silicon-oxide-nitride-oxide-silicon structure comprising a first oxide layer arranged upon a silicon-based semiconductor substrate, wherein an interface between the silicon-based semiconductor substrate and the first oxide layer comprises deuterium.

18. (Original) The silicon-oxide-nitride-oxide-silicon structure of claim 17, wherein a lateral length of the interface between the silicon-based semiconductor substrate and the first oxide layer is bound by opposing sidewalls of the structure, and wherein said deuterium is arranged across an entirety of said lateral length.

19. (Original) The silicon-oxide-nitride-oxide-silicon structure of claim 17, further comprising:

a nitride layer arranged upon and in contact with the first oxide layer;

a second oxide layer arranged upon and in contact with the nitride layer; and

a second silicon layer arranged upon and in contact with the second oxide layer, wherein an interface between the second silicon layer and second oxide layer comprises deuterium.

20. (Original) The silicon-oxide-nitride-oxide-silicon structure of claim 19, wherein said nitride layer comprises deuterium.